

Abstract

To provide a vibrating device excellent in frequency temperature characteristics and resistant to reduction in a Q value. In a vibrating device 1 using a bending vibration mode, vibrating arms 3a, 3b, and 3c are connected to a supporter 2, the vibrating arms 3a, 3b, and 3c have an n-type Si layer 11 which is a degenerated semiconductor and an exciter 14 provided on the n-type Si layer 11, and the exciter 14 has a piezoelectric thin film 15 and a first and second electrodes 16 and 17 with the piezoelectric thin film 15 interposed therebetween.